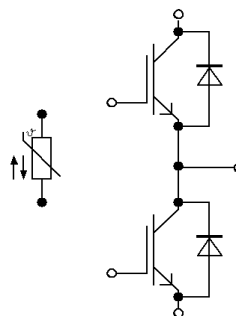


PrimePACK™2 模块 采用第五代沟槽栅/场终止IGBT5和第五代发射极控制二极管 带有温度检测NTC
 PrimePACK™2 module with Trench/Fieldstop IGBT5, Emitter Controlled 5 diode and NTC



$V_{CES} = 1200V$
 $I_{C\ nom} = 1200A / I_{CRM} = 2400A$

典型应用

- 大功率变流器
- 电机传动
- UPS系统

Typical Applications

- High power converters
- Motor drives
- UPS systems

电气特性

- 提高工作结温 $T_{vj\ op}$
- 高短路能力
- 无与伦比的坚固性
- $T_{vj\ op} = 175^{\circ}C$
- 沟槽栅IGBT5

Electrical Features

- Extended operating temperature $T_{vj\ op}$
- High short-circuit capability
- Unbeatable robustness
- $T_{vj\ op} = 175^{\circ}C$
- Trench IGBT 5

机械特性

- 封装的 CTI > 400
- 高爬电距离和电气间隙
- 高功率循环和温度循环能力
- 高功率密度

Mechanical Features

- Package with CTI > 400
- High creepage and clearance distances
- High power and thermal cycling capability
- High power density

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	$T_C = 80^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$	1200	A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	2400	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

		min.	typ.	max.		
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 1200\text{ A}, V_{GE} = 15\text{ V}$		1,70	2,15	V	
	$I_C = 1200\text{ A}, V_{GE} = 15\text{ V}$		2,00	2,45	V	
	$I_C = 1200\text{ A}, V_{GE} = 15\text{ V}$		2,15	2,60	V	
栅极阈值电压 Gate threshold voltage	$I_C = 33,0\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$	V_{GEth}	5,25	5,80	6,35	V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}, V_{CE} = 600\text{ V}$	Q_G		5,75		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$	R_{Gint}		0,75		Ω
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$	C_{ies}		65,5		nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$	C_{res}		2,60		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$	I_{CES}			5,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$	I_{GES}			400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 1200\text{ A}, V_{CE} = 600\text{ V}$			0,20		μs
	$V_{GE} = \pm 15\text{ V}$			0,23		μs
	$R_{Gon} = 0,82\ \Omega$			0,25		μs
上升时间(电感负载) Rise time, inductive load	$I_C = 1200\text{ A}, V_{CE} = 600\text{ V}$			0,16		μs
	$V_{GE} = \pm 15\text{ V}$			0,17		μs
	$R_{Gon} = 0,82\ \Omega$			0,18		μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 1200\text{ A}, V_{CE} = 600\text{ V}$			0,48		μs
	$V_{GE} = \pm 15\text{ V}$			0,52		μs
	$R_{Goff} = 0,82\ \Omega$			0,55		μs
下降时间(电感负载) Fall time, inductive load	$I_C = 1200\text{ A}, V_{CE} = 600\text{ V}$			0,08		μs
	$V_{GE} = \pm 15\text{ V}$			0,11		μs
	$R_{Goff} = 0,82\ \Omega$			0,13		μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 1200\text{ A}, V_{CE} = 600\text{ V}, L_S = 45\text{ nH}$			80,0		mJ
	$V_{GE} = \pm 15\text{ V}, di/dt = 6000\text{ A}/\mu\text{s} (T_{vj} = 175^{\circ}\text{C})$			120		mJ
	$R_{Gon} = 0,82\ \Omega$			160		mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 1200\text{ A}, V_{CE} = 600\text{ V}, L_S = 45\text{ nH}$			130		mJ
	$V_{GE} = \pm 15\text{ V}, du/dt = 2800\text{ V}/\mu\text{s} (T_{vj} = 175^{\circ}\text{C})$			160		mJ
	$R_{Goff} = 0,82\ \Omega$			180		mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 900\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	I_{SC}		4000		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT	R_{thJC}			28,7	K/kW
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$	R_{thCH}			22,1	K/kW
在开关状态下温度 Temperature under switching conditions		$T_{vj\text{op}}$	-40		175	$^{\circ}\text{C}$

二极管, 逆变器 / Diode, Inverter 最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	1200	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	2400	A
I ² t-值 I ² t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$	I ² t	370	kA ² s
	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 175^{\circ}\text{C}$		335	kA ² s

特征值 / Characteristic Values

				min.	typ.	max.	
正向电压 Forward voltage	$I_F = 1200\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	V_F		1,90	2,45	V
	$I_F = 1200\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$			1,75	2,30	V
	$I_F = 1200\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 175^{\circ}\text{C}$			1,70	2,25	V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 1200\text{ A}, -di_F/dt = 6600\text{ A}/\mu\text{s} (T_{vj}=175^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	I_{RM}		630		A
		$T_{vj} = 125^{\circ}\text{C}$			860		A
		$T_{vj} = 175^{\circ}\text{C}$			985		A
恢复电荷 Recovered charge	$I_F = 1200\text{ A}, -di_F/dt = 6600\text{ A}/\mu\text{s} (T_{vj}=175^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	Q_r		91,0		μC
		$T_{vj} = 125^{\circ}\text{C}$			205		μC
		$T_{vj} = 175^{\circ}\text{C}$			280		μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 1200\text{ A}, -di_F/dt = 6600\text{ A}/\mu\text{s} (T_{vj}=175^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	E_{rec}		37,0		mJ
		$T_{vj} = 125^{\circ}\text{C}$			83,0		mJ
		$T_{vj} = 175^{\circ}\text{C}$			120		mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode	R_{thJC}			46,3	K/kW	
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$	R_{thCH}			29,0	K/kW	
在开关状态下温度 Temperature under switching conditions		$T_{vj\text{ op}}$	-40		175	$^{\circ}\text{C}$	

负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

				min.	typ.	max.	
额定电阻值 Rated resistance	$T_{NTC} = 25^{\circ}\text{C}$	R_{25}			5,00		k Ω
R100 偏差 Deviation of R100	$T_{NTC} = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$	$\Delta R/R$	-5		5		%
耗散功率 Power dissipation	$T_{NTC} = 25^{\circ}\text{C}$	P_{25}			20,0		mW
B-值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/50}$			3375		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/80}$			3411		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/100}$			3433		K

根据应用手册标定

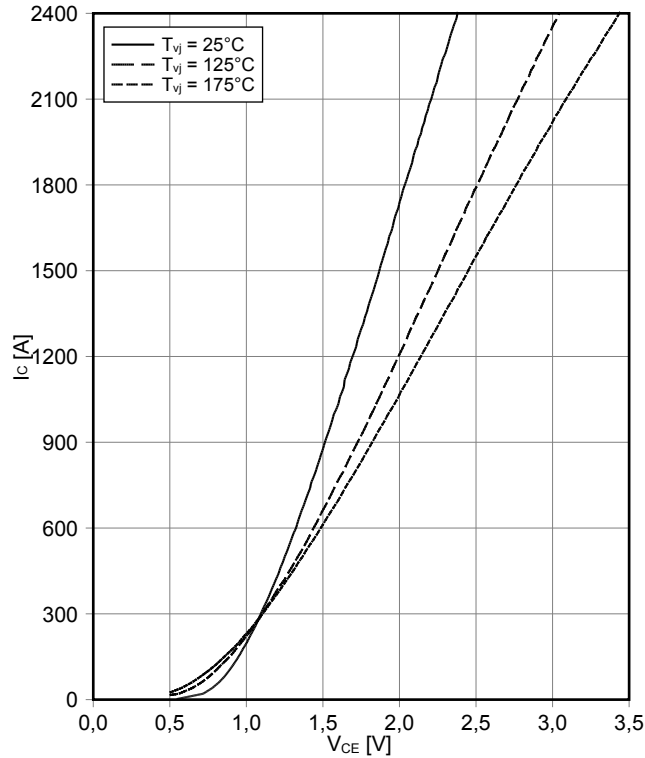
Specification according to the valid application note.

模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	4,0		kV
模块基板材料 Material of module baseplate			Cu		
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃		
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		33,0 33,0		mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		19,0 19,0		mm
相对电痕指数 Comperative tracking index		CTI	> 400		
			min.	typ.	max.
杂散电感, 模块 Stray inductance module		L _{sCE}		18	nH
模块引线电阻, 端子-芯片 Module lead resistance, terminals - chip	T _c = 25°C, 每个开关 / per switch	R _{CC'+EE'} R _{AA'+CC'}		0,15 0,09	mΩ
储存温度 Storage temperature		T _{stg}	-40		150 °C
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M5 根据相应的应用手册进行安装 Screw M5 - Mounting according to valid application note	M	3,00		6,00 Nm
端子联接扭矩 Terminal connection torque	螺丝 M4 根据相应的应用手册进行安装 Screw M4 - Mounting according to valid application note 螺丝 M8 根据相应的应用手册进行安装 Screw M8 - Mounting according to valid application note	M	1,8 8,0	- -	2,1 10 Nm
重量 Weight		G		825	g

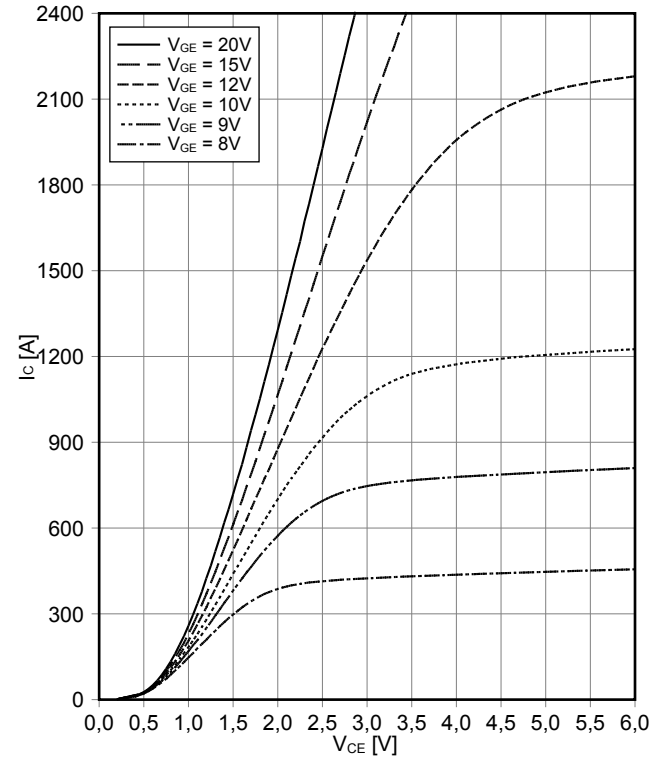
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



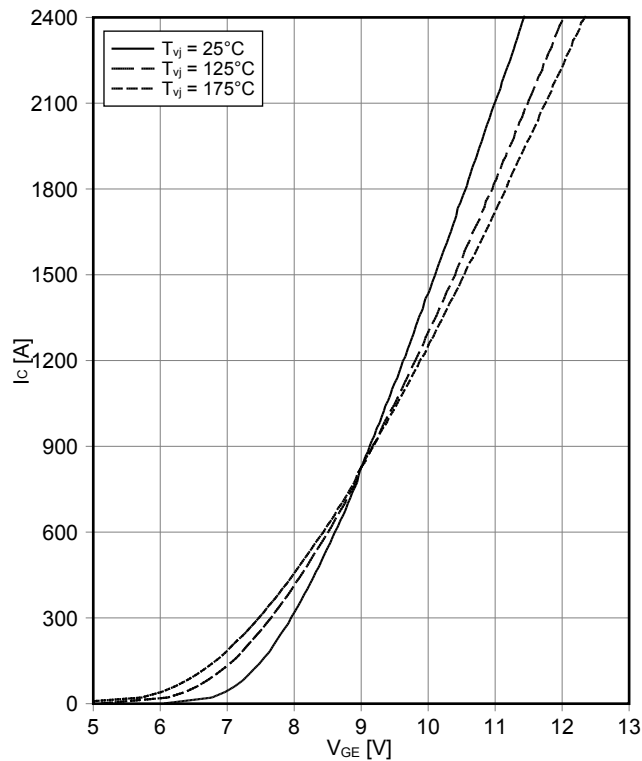
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 175^\circ\text{C}$



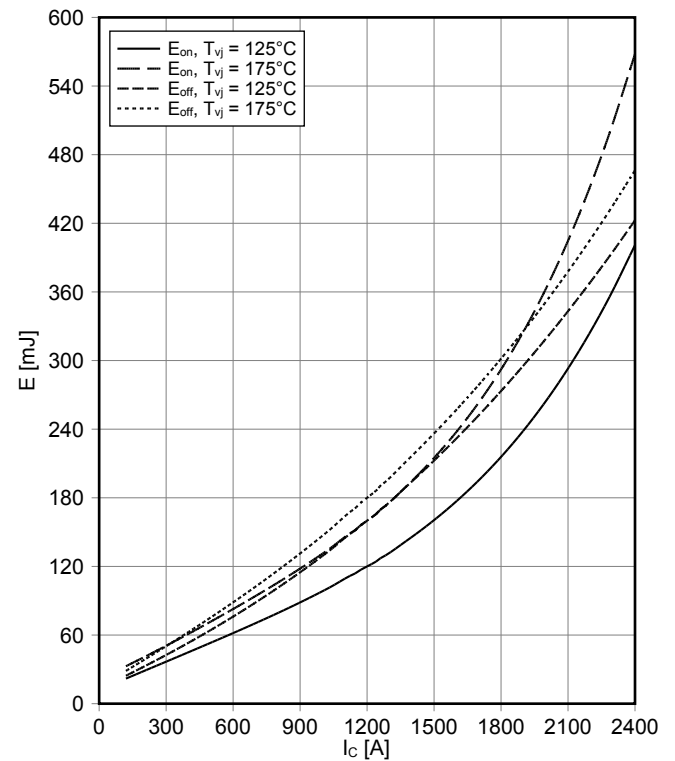
传输特性 IGBT, 逆变器 (典型)
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



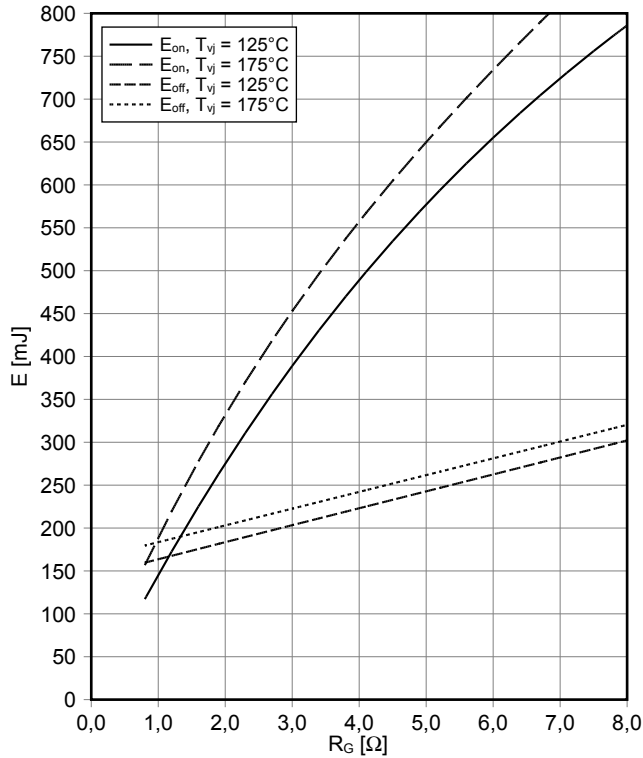
开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 0.82\ \Omega$, $R_{Goff} = 0.82\ \Omega$, $V_{CE} = 600\text{ V}$



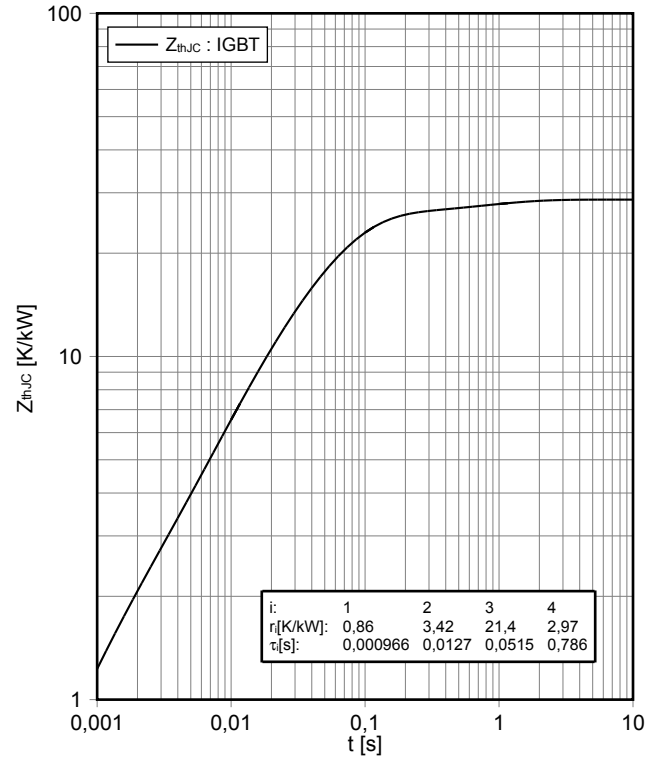
开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}, I_C = 1200\text{ A}, V_{CE} = 600\text{ V}$



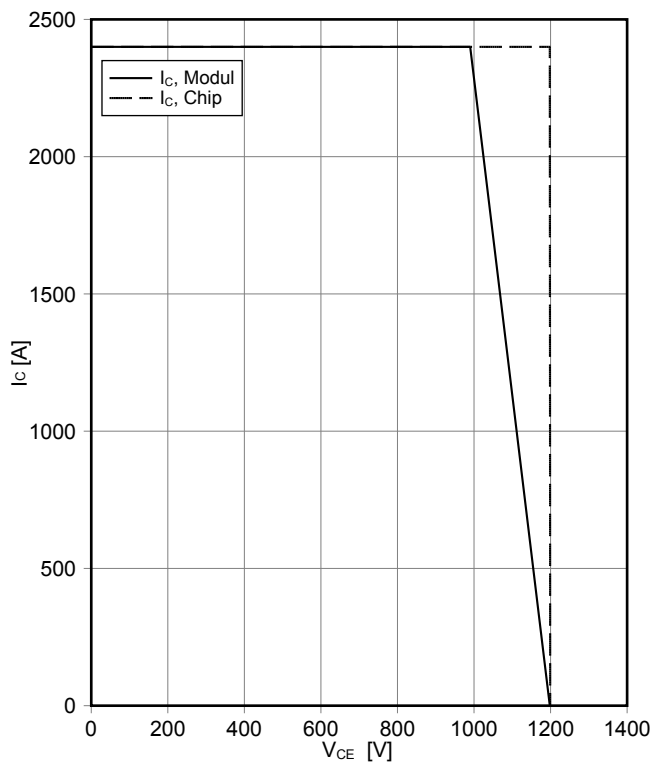
瞬态热阻抗 IGBT, 逆变器
transient thermal impedance IGBT, Inverter

$Z_{thJC} = f(t)$



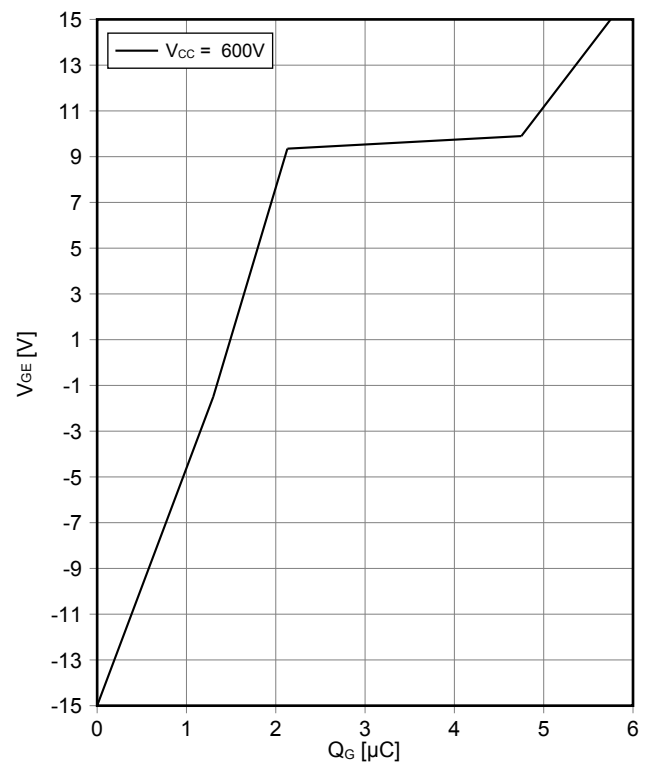
反偏安全工作区 IGBT, 逆变器 (RBSOA)
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}, R_{Goff} = 0.82\ \Omega, T_{vj} = 175^\circ\text{C}$

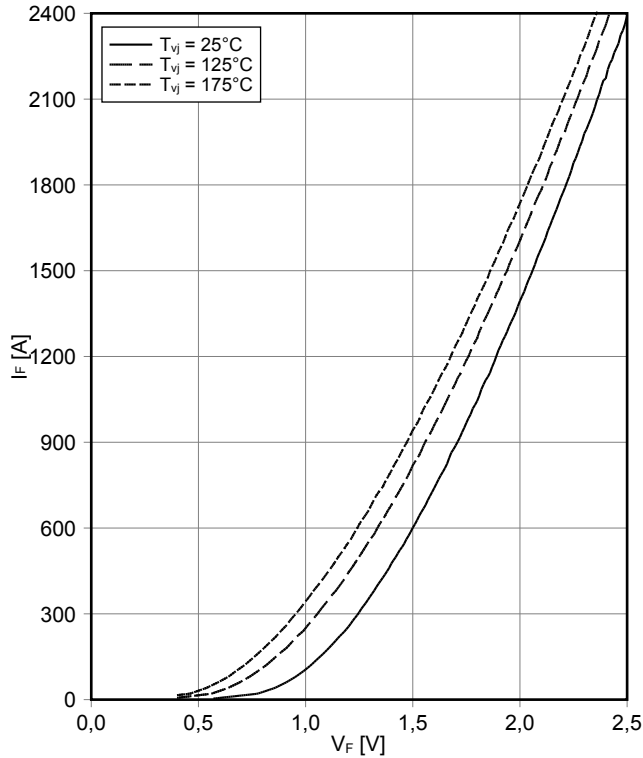


栅极电荷特性 IGBT, 逆变器 (典型)
gate charge characteristic IGBT, Inverter (typical)

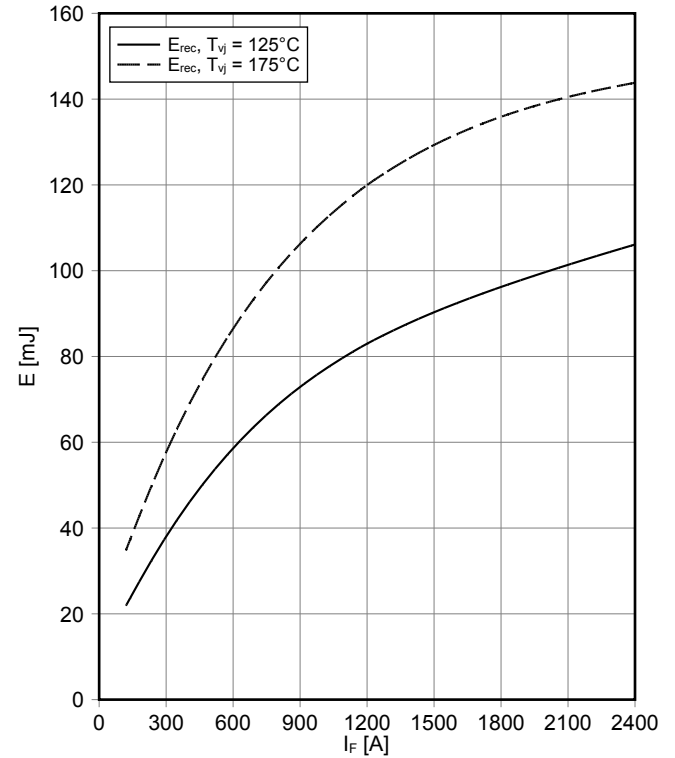
$V_{GE} = f(Q_G)$
 $I_C = 1200\text{ A}, T_{vj} = 25^\circ\text{C}$



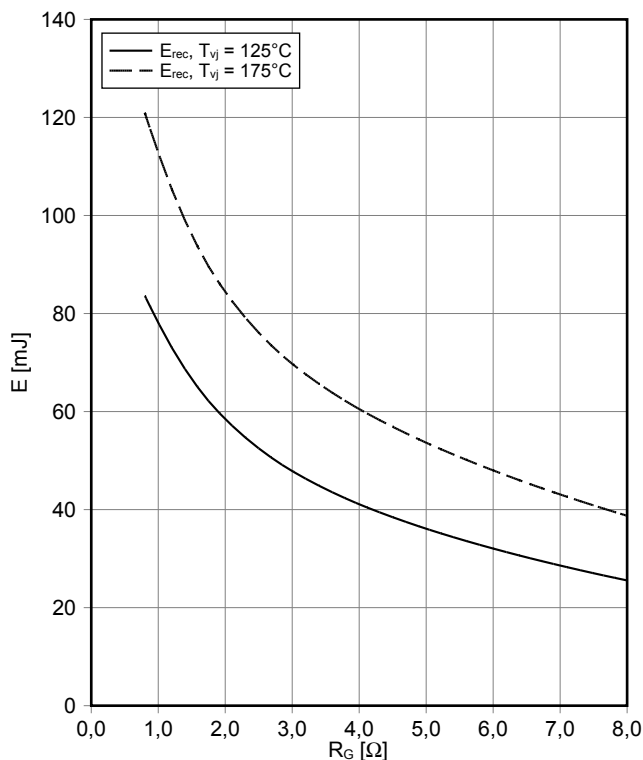
正向偏压特性 二极管,逆变器 (典型)
forward characteristic of Diode, Inverter (typical)
 $I_F = f(V_F)$



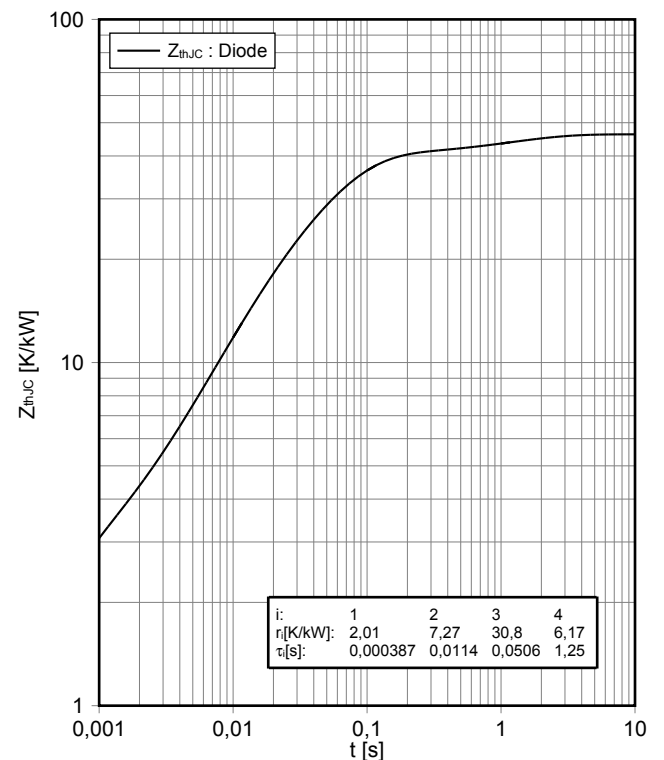
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)
 $E_{rec} = f(I_F)$
 $R_{Gon} = 0.82 \Omega, V_{CE} = 600 \text{ V}$



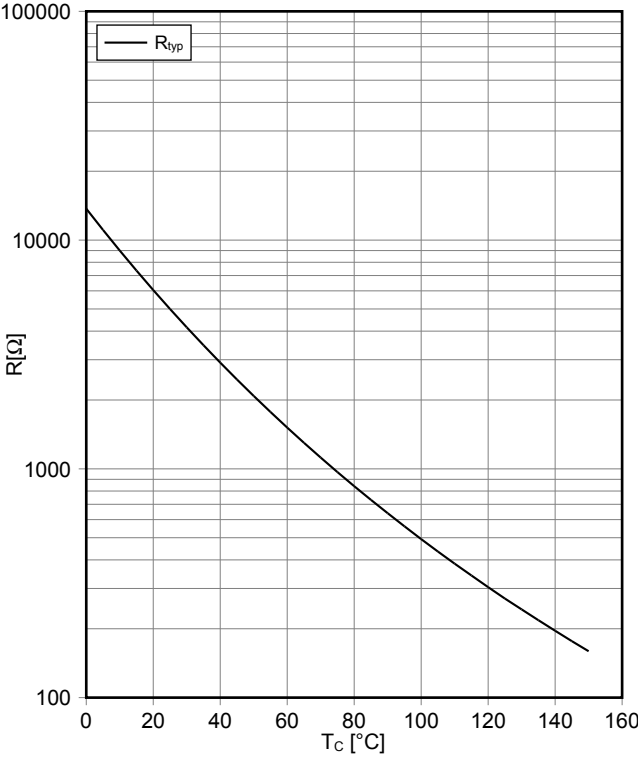
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)
 $E_{rec} = f(R_G)$
 $I_F = 1200 \text{ A}, V_{CE} = 600 \text{ V}$



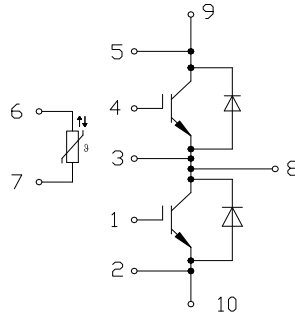
瞬态热阻抗 二极管,逆变器
transient thermal impedance Diode, Inverter
 $Z_{thJC} = f(t)$



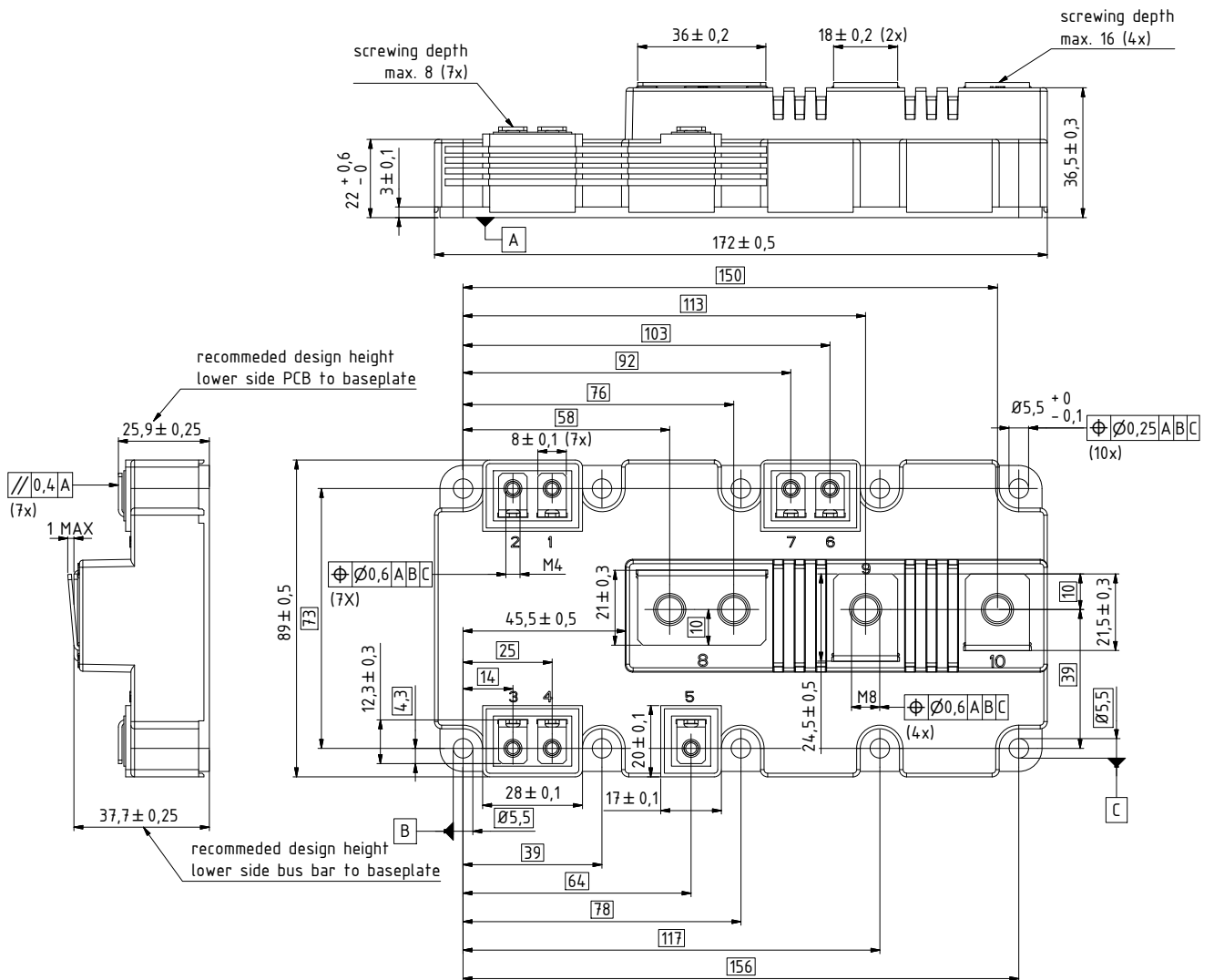
负温度系数热敏电阻 温度特性
NTC-Thermistor-temperature characteristic (typical)
 $R = f(T)$



接线图 / Circuit diagram



封装尺寸 / Package outlines



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